

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S60	14	08/707491	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/27 18:44
S62	7995	fluorine same S61	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/27 18:59
S61	667820	(gate with insulating with (film layer)) (insulating with (film layer)) (gate with dielectric) (gate with insulator) (gate near oxide)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/27 18:59
S65	349	S63 and S64	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/27 19:00
S64	139272	(thin with film with transistor) TFT	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/27 19:00
S63	1536	(concentration amount atoms) same S62	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/27 19:00
S66	2	("6875674").PN.	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/08/27 19:06
S67	3881	amorphous near2 (SiN (silicon near nitride) "Si.sub"\$N.sub"\$4)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/27 19:22
S70	17	S69 same fluorine same (concentration amount atoms)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/27 19:23

S69	4156	S67 S68	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/27 19:23
S68	383	a-SiN "a-Si.sub"\$N. sub"\$4 "a - Si.sub"\$N. sub"\$4 "a - Si.sub"\$N. sub"\$4 "a - Si.sub"\$N. sub"\$4	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/27 19:23
S71	18	S69 same fluorine same (concentration amount atoms quantity dose)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/27 20:10
L5	468976	pixel	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/29 11:16
L4	4159	L2 L3	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/29 11:16
L3	383	a-SiN "a-Si.sub"\$N. sub"\$4 "a - Si.sub"\$N. sub"\$4 "a - Si.sub"\$N. sub"\$4 "a - Si.sub"\$N. sub"\$4	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/29 11:16
L2	3884	amorphous near2 (SiN (silicon near nitride) "Si. sub"\$N.sub"\$4)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/29 11:16
L1	139438	(thin with film with transistor) TFT	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/29 11:16
L6	584039	LCD (liquid near crystal near display)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/29 11:17
L16	2	("20020117691").PN.	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/08/29 11:19

8/29/2008 12:16:41 PM

C:\Documents and Settings\ETaylor\My Documents\EAST\Workspaces\10595640 Transistor having a gate insulating film containing fluorine.wsp